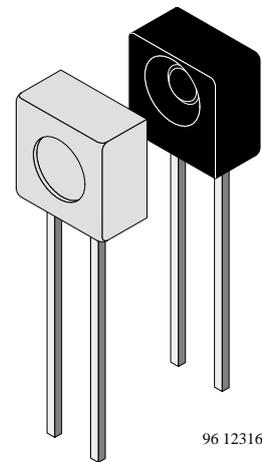


Matchable Pairs – Emitter and Detector

Description

Pairs of infrared-emitting diode and phototransistor, matched in their optical and electrical features. These pairs enable a lot of applications. They can be used both for transmissive or reflective sensor functions. The peak wavelength of the emitter is $\lambda = 950 \text{ nm}$.



Applications

Generally used for industrial processing and controlling, end of tape detector

Features

- Miniature case with lens
- Detector with optical filter, protected against ambient light
- Detector case black for easy identification of the emitter and detector
- Emitter-angle of half-intensity $\pm\varphi = 35^\circ$
- Detector-angle of half sensitivity $\varphi = 35^\circ$
- Emitter and detector in sideview case
- High CTR $\geq 5\%$

Absolute Maximum Ratings

Input (Emitter)

Parameters	Test Conditions	Symbol	Value	Unit
Reverse voltage		V_R	6	V
Forward current		I_F	60	mA
Forward surge current	$t_p \leq 10 \mu s$	I_{FSM}	1	A
Power dissipation	$T_{amb} \leq 25^\circ C$	P_V	100	mW
Junction temperature		T_j	100	$^\circ C$

Output (Detector)

Parameters	Test Conditions	Symbol	Value	Unit
Collector emitter voltage		V_{CEO}	70	V
Emitter collector voltage		V_{ECO}	7	V
Collector current		I_C	50	mA
Collector peak current	$t_p/T = 0.5, t_p \leq 10 \text{ ms}$	I_{CM}	100	mA
Power dissipation	$T_{amb} \leq 25^\circ C$	P_V	150	mW
Junction temperature		T_j	100	$^\circ C$

Coupler

Parameters	Test Conditions	Symbol	Value	Unit
Operating temperature range		T_{amb}	-55 to +85	$^\circ C$
Storage temperature range		T_{stg}	-55 to +100	$^\circ C$
Soldering temperature	2 mm from case, $t \leq 5 \text{ s}$	T_{sd}	260	$^\circ C$

Electrical Characteristics

$T_{amb} = 25^\circ C$

Input (Emitter)

Parameters	Test Conditions	Symbol	Min.	Typ.	Max.	Unit
Forward voltage	$I_F = 50 \text{ mA}$	V_F		1.25	1.6	V
Breakdown voltage	$I_R = 100 \mu A$	$V_{(BR)}$	5			V
Junction capacitance	$V_R = 0, f = 1 \text{ MHz}$	C_j		50		pF

Output (Detector)

Parameters	Test Conditions	Symbol	Min.	Typ.	Max.	Unit
Collector emitter breakdown voltage	$I_C = 1 \text{ mA}$	$V_{(BR)CEO}$	70			V
Emitter collector breakdown voltage	$I_C = 100 \mu A$	$V_{(BR)ECO}$	7			V
Collector dark current	$V_{CE} = 25 \text{ V}, I_f = 0, E = 0$	I_{CEO}			100	nA

Emitter and Detector matched

Parameters	Test Conditions	Symbol	Min.	Typ.	Max.	Unit
Collector current	$I_F = 20 \text{ mA}$, $V_{CE} = 5 \text{ V}$	I_C	1	2		mA
I_C/I_F	$I_F = 20 \text{ mA}$, $V_{CE} = 5 \text{ V}$	CTR	0.5	1		
Collector emitter saturation voltage	$I_F = 20 \text{ mA}$, $I_C = 0.1 \text{ mA}$	V_{CEsat}			0.4	V
Cut-off frequency	$I_F = 10 \text{ mA}$, $V_{CE} = 5 \text{ V}$, $R_L = 100 \Omega$	f_C		110		kHz
Coupling capacitance	$f = 1 \text{ MHz}$	C_k		0.3		pF

Switching Characteristics

$V_S = 5 \text{ V}$

Type	$R_L = 100 \Omega$ (see figure 1)						$R_L = 1 \text{ k}\Omega$			
	$t_d[\mu\text{s}]$	$t_r[\mu\text{s}]$	$t_{on}[\mu\text{s}]$	$t_s[\mu\text{s}]$	$t_f[\mu\text{s}]$	$t_{off}[\mu\text{s}]$	$I_C[\text{mA}]$	$t_{on}[\mu\text{s}]$	$t_{off}[\mu\text{s}]$	$I_F[\text{mA}]$
TCZT8012			10			8	2			

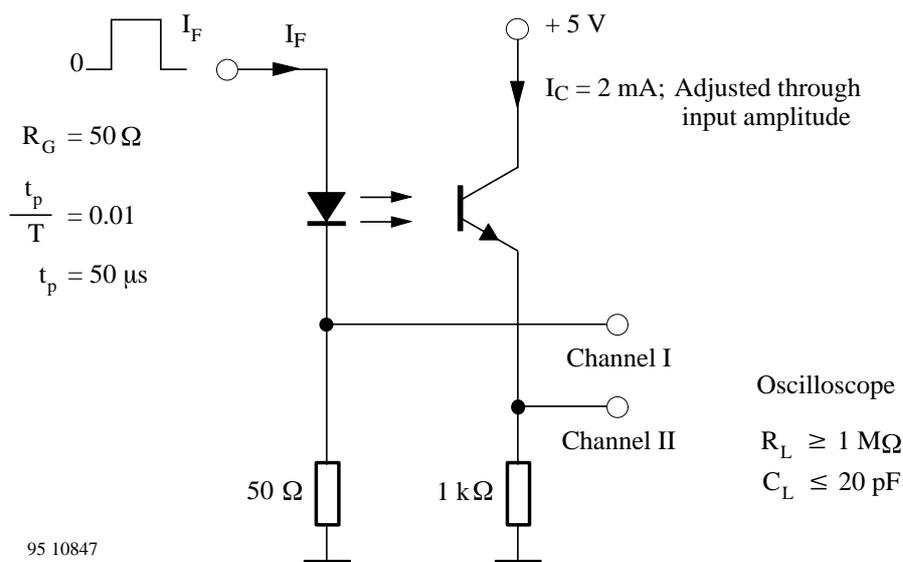


Figure 1. Test circuit

Typical Characteristics ($T_{amb} = 25^{\circ}\text{C}$, unless otherwise specified)

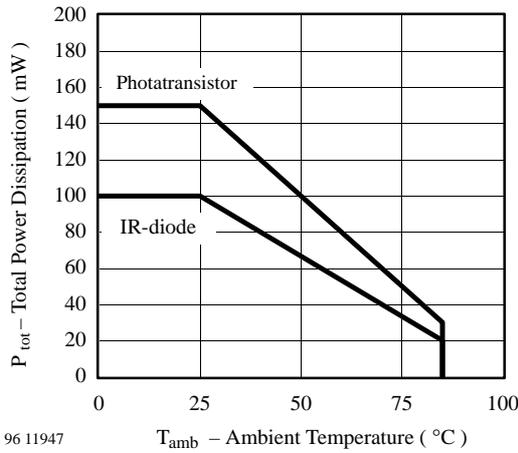


Figure 2. Total Power Dissipation vs. Ambient Temperature

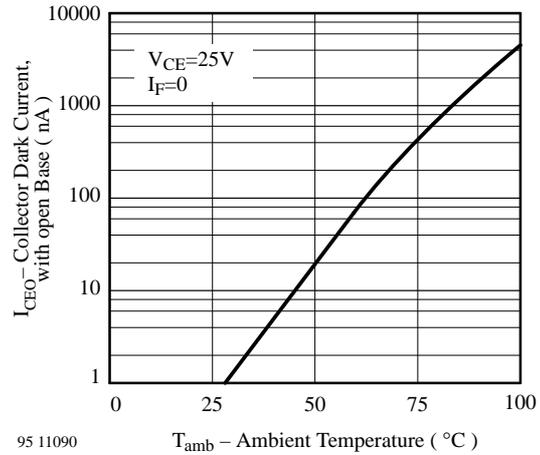


Figure 5. Collector Dark Current vs. Ambient Temperature

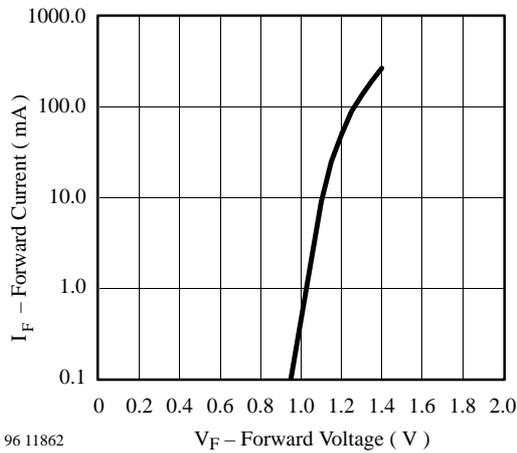


Figure 3. Forward Current vs. Forward Voltage

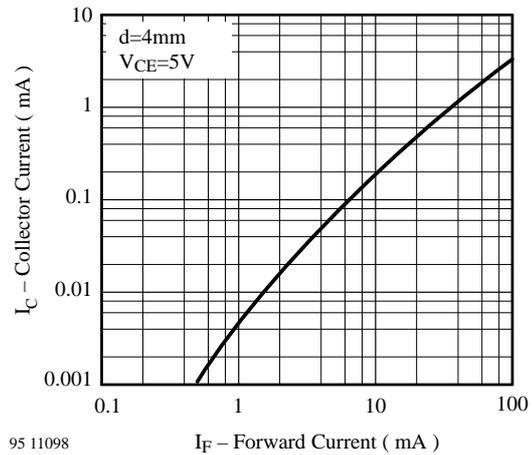


Figure 6. Collector Current vs. Forward Current

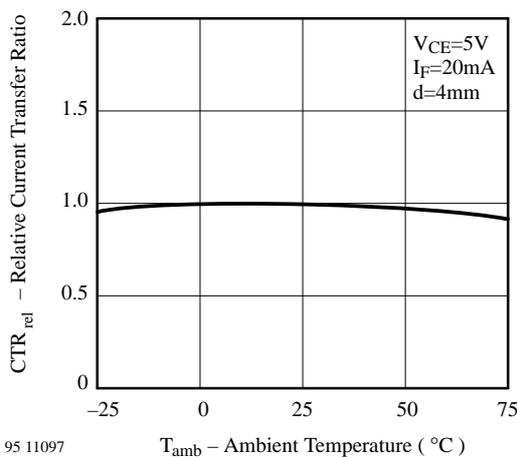


Figure 4. Rel. Current Transfer Ratio vs. Ambient Temperature

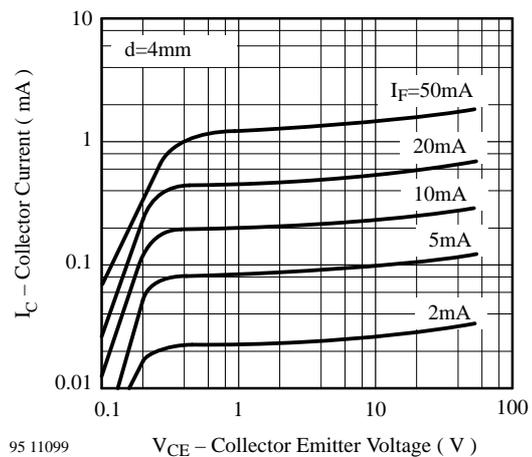


Figure 7. Collector Current vs. Collector Emitter Voltage

Typical Characteristics ($T_{amb} = 25^{\circ}C$, unless otherwise specified)

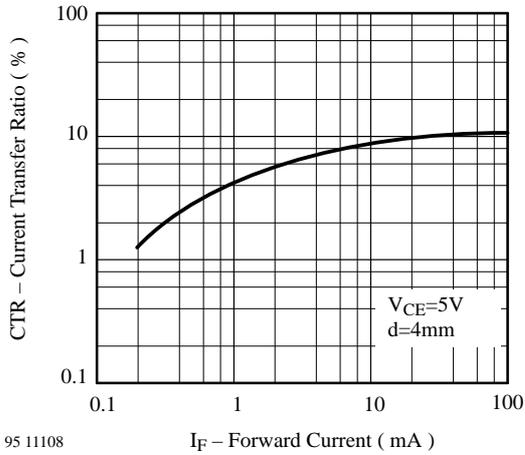


Figure 8. Current Transfer Ratio vs. Forward Current

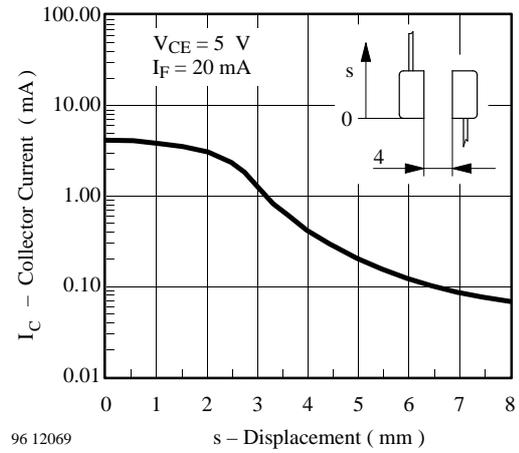


Figure 11. Collector Current vs. Displacement

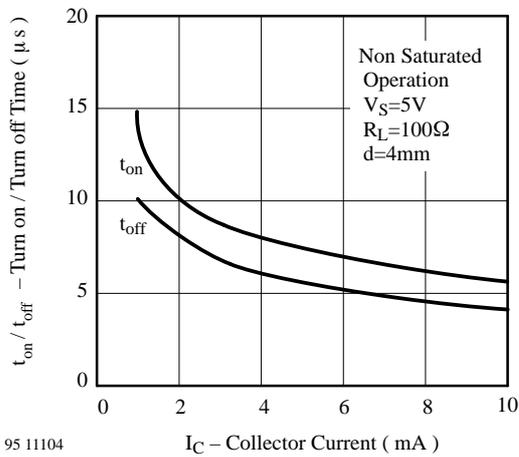


Figure 9. Turn on / off Time vs. Collector Current

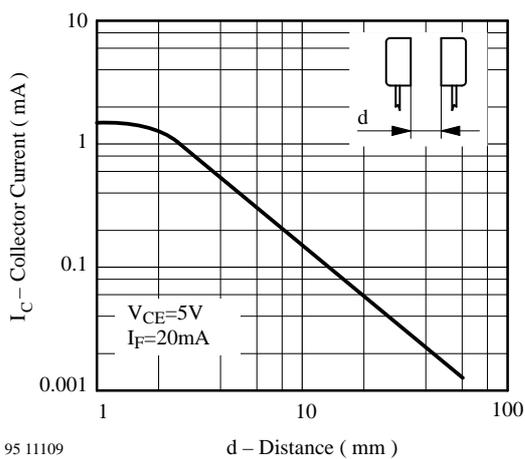
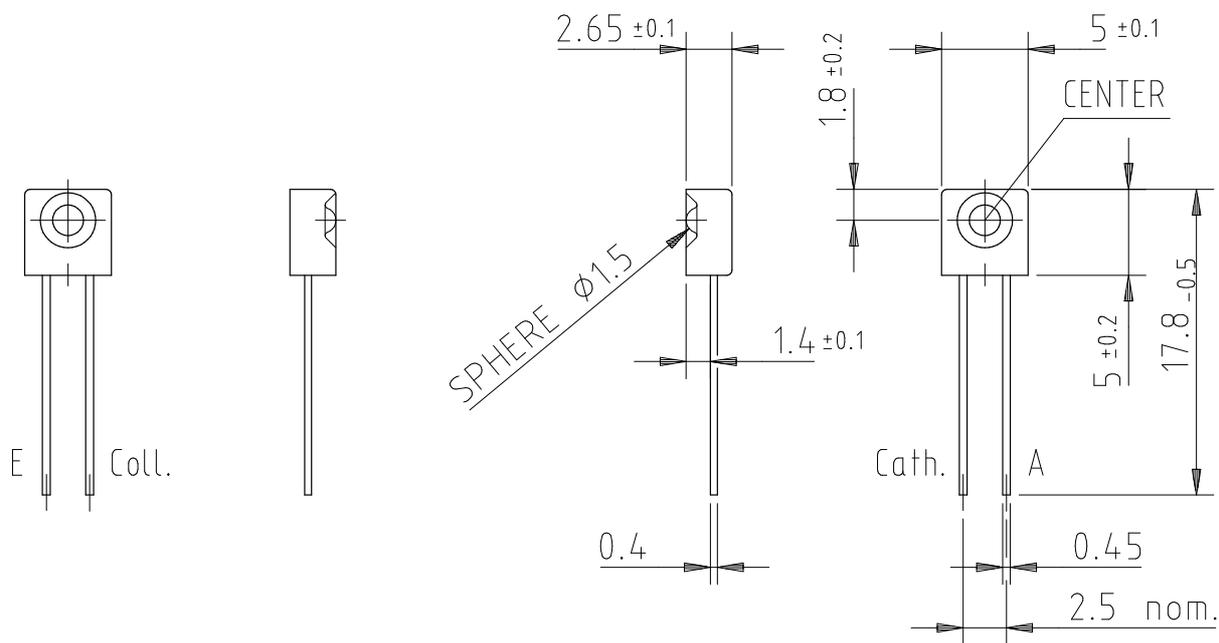


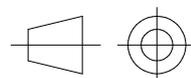
Figure 10. Collector Current vs. Distance

Dimensions in mm



DETECTOR (BLACK)

EMITTER (CLEAR)



technical drawings
according to DIN
specifications

96 12105

Ozone Depleting Substances Policy Statement

It is the policy of **TEMIC TELEFUNKEN microelectronic GmbH** to

1. Meet all present and future national and international statutory requirements.
2. Regularly and continuously improve the performance of our products, processes, distribution and operating systems with respect to their impact on the health and safety of our employees and the public, as well as their impact on the environment.

It is particular concern to control or eliminate releases of those substances into the atmosphere which are known as ozone depleting substances (ODSs).

The Montreal Protocol (1987) and its London Amendments (1990) intend to severely restrict the use of ODSs and forbid their use within the next ten years. Various national and international initiatives are pressing for an earlier ban on these substances.

TEMIC TELEFUNKEN microelectronic GmbH semiconductor division has been able to use its policy of continuous improvements to eliminate the use of ODSs listed in the following documents.

1. Annex A, B and list of transitional substances of the Montreal Protocol and the London Amendments respectively
2. Class I and II ozone depleting substances in the Clean Air Act Amendments of 1990 by the Environmental Protection Agency (EPA) in the USA
3. Council Decision 88/540/EEC and 91/690/EEC Annex A, B and C (transitional substances) respectively.

TEMIC can certify that our semiconductors are not manufactured with ozone depleting substances and do not contain such substances.

We reserve the right to make changes to improve technical design and may do so without further notice.

Parameters can vary in different applications. All operating parameters must be validated for each customer application by the customer. Should the buyer use TEMIC products for any unintended or unauthorized application, the buyer shall indemnify TEMIC against all claims, costs, damages, and expenses, arising out of, directly or indirectly, any claim of personal damage, injury or death associated with such unintended or unauthorized use.

TEMIC TELEFUNKEN microelectronic GmbH, P.O.B. 3535, D-74025 Heilbronn, Germany
Telephone: 49 (0)7131 67 2831, Fax number: 49 (0)7131 67 2423